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Introduction

The 16th edition of the biennial series of International Workshop on the Physics of Semiconductor Devices (IWPSD) was organized by IIT Kanpur and the Society for Semiconductor Devices (SSD). For the last three decades, this workshop has become the most prestigious of international events associated with semiconductor devices in India. The series has become an important forum for the community and its international linkages, and for every new generation of participants, as an eagerly awaited event to keep pace with the topicality and frontiers of change within this broad highly interdisciplinary area.

The Organizing Committee with the help of Technical Programme Committees had put together nine different symposia, which are truly topical. The representative character of the Workshop has been improved in all the parameters of interest that we had set for ourselves. In all, about 550 delegates participated in the deliberations, which included eight plenary speakers, 100 invited speakers in four parallel sessions each day, and 367 contributed papers. The participants came from 16 different countries, and about 60 per cent of the invited speakers were from abroad. Semiconductor Devices is one area which prospers on the basis of close interaction of academics with industry, and we were happy to note the enthusiastic participation of industry.

The Programme Committee and the Printing and Publications Committee has worked hard to put together this volume, ably supported by SPIE publications division. As an editorial board, we have kept in view the scientific quality of the papers submitted for inclusion in the volume. We have limited means of correcting or influencing the language and expression in the articles, although we have tried to point out to the authors wherever a major revision in language was needed.

We are especially thankful to Dr. Vandana Singh at IIT Kanpur, for having put in much of the hard work needed for coordination at all stages of the production of this volume, aided by the team responsible for publications.

Compiling a Proceedings of selected papers in the Workshop of this magnitude has been possible only because of toils of a band of dedicated faculty members at IIT Kanpur and referees in many other Institutions across the globe. We had to go through many successive delays in producing this volume, due to several organizational difficulties on the way. But the final outcome would be worth the effort to the community.

Y. N. Mohapatra
Chair, IWPSD – 2011